

CLAIMS

1. For semiconductor manufacturing equipment, a ceramic susceptor having in the surface or interior of its ceramic substrate a resistive heating element, the ceramic susceptor for semiconductor manufacturing equipment characterized in that its wafer-carrying face in arched contour when not heating is a concavity of 0.001 to 0.7 mm/300 mm.
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2. A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 1, characterized in that the ceramic substrate is made of at least one ceramic selected from aluminum nitride, silicon nitride, aluminum oxynitride, and silicon carbide.
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3. A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 1 or 2, characterized in that the resistive heating element is made from at least one metal selected from tungsten, molybdenum, platinum, palladium, silver, nickel, and chrome.
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4. A semiconductor-manufacturing-equipment ceramic susceptor as set forth in any of claims 1 through 3, characterized in that a plasma electrode furthermore is disposed in the surface or interior of the ceramic substrate.